



Standard Rectifier

$V_{RRM} = 1600\text{ V}$

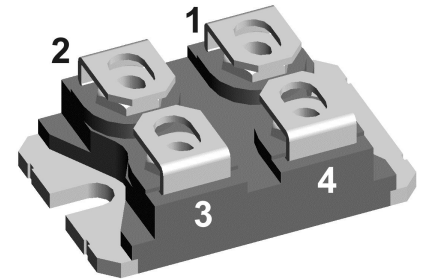
$I_{FAV} = 2 \times 100\text{ A}$

$V_F = 1.21\text{ V}$

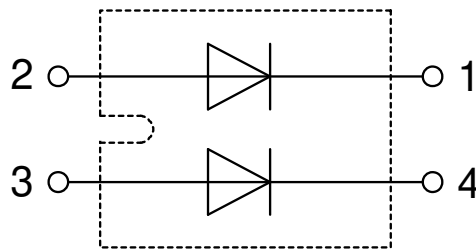
Parallel legs

Part number

DMA200X1600NA



Backside: isolated



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

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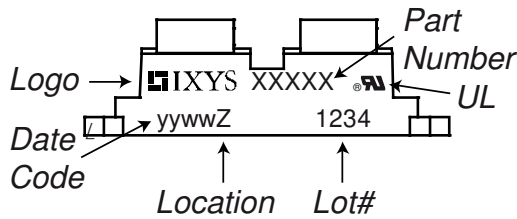


Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1700	V
V_{RRM}	max. repetitive reverse blocking voltage					1600	V
I_R	reverse current	$V_R = 1600$ V		$T_{VJ} = 25^\circ\text{C}$		200	μA
		$V_R = 1600$ V		$T_{VJ} = 150^\circ\text{C}$		2	mA
V_F	forward voltage drop	$I_F = 100$ A		$T_{VJ} = 25^\circ\text{C}$		1.24	V
		$I_F = 200$ A				1.55	V
		$I_F = 100$ A		$T_{VJ} = 125^\circ\text{C}$		1.21	V
		$I_F = 200$ A				1.61	V
I_{FAV}	average forward current	$T_C = 100^\circ\text{C}$		$T_{VJ} = 150^\circ\text{C}$		100	A
		rectangular	d = 0.5				
V_{FO}	threshold voltage			$T_{VJ} = 150^\circ\text{C}$		0.80	V
r_F	slope resistance					4	m Ω
R_{thJC}	thermal resistance junction to case					0.3	K/W
R_{thCH}	thermal resistance case to heatsink				0.1		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		415	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		1.50	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		1.62	kA
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		1.28	kA
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		1.38	kA
I^2t	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		11.3	kA ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		10.9	kA ² s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		8.13	kA ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		7.87	kA ² s
C_J	junction capacitance	$V_R = 400$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		53	pF



Package SOT-227B (minibloc)		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			150	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1.1		1.5	Nm
M_T	terminal torque		1.1		1.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/Apb}$		terminal to backside	8.6	6.8		mm
V_{ISOL}	isolation voltage	t = 1 second		3000		V
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500		V

Product Marking



Part description

- D = Diode
- M = Standard Rectifier
- A = (up to 1800V)
- 200 = Current Rating [A]
- X = Parallel legs
- 1600 = Reverse Voltage [V]
- NA = SOT-227B (minibloc)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DMA200X1600NA	DMA200X1600NA	Tube	10	518461

Similar Part	Package	Voltage class
DMA200XA1600NA	SOT-227B (minibloc)	1600
DAA200X1800NA	SOT-227B (minibloc)	1800
DAA200XA1800NA	SOT-227B (minibloc)	1800

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$



Rectifier

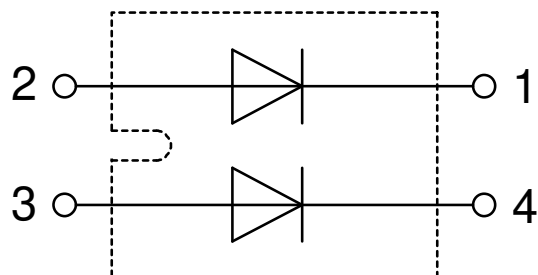
$V_{0\ max}$	threshold voltage	0.8	V
$R_{0\ max}$	slope resistance *	2.2	mΩ



Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



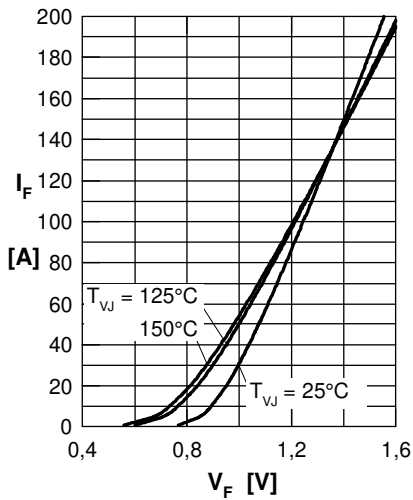
Rectifier


Fig. 1 Forward current versus voltage drop per diode

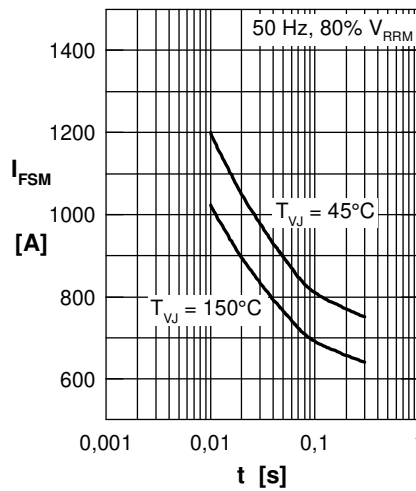


Fig. 2 Surge overload current

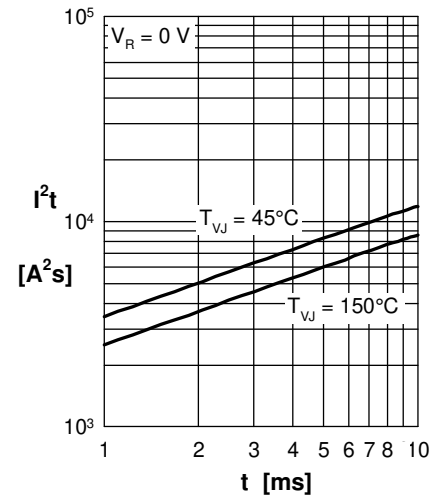
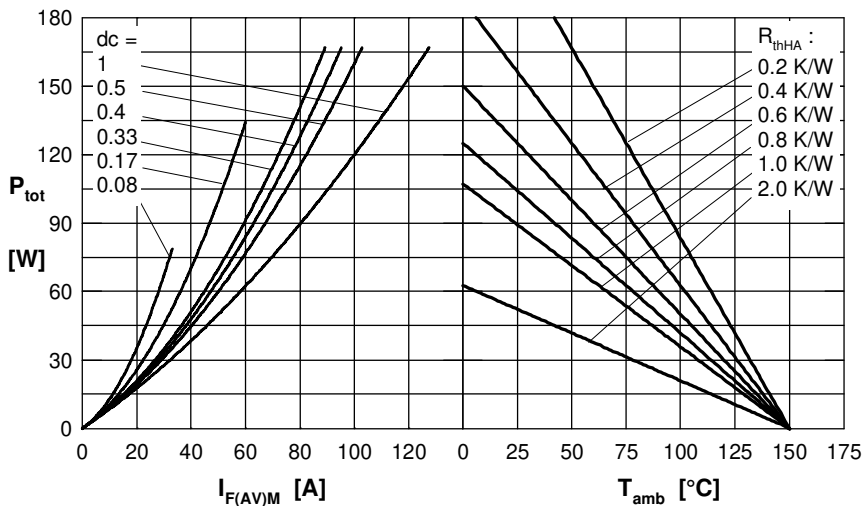

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. direct output current & ambient temperature

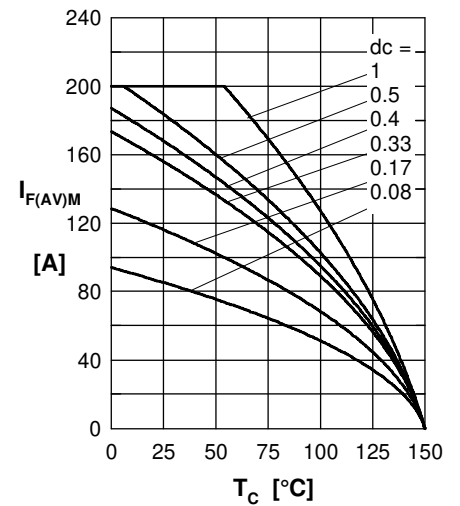


Fig. 5 Max. forward current versus case temperature

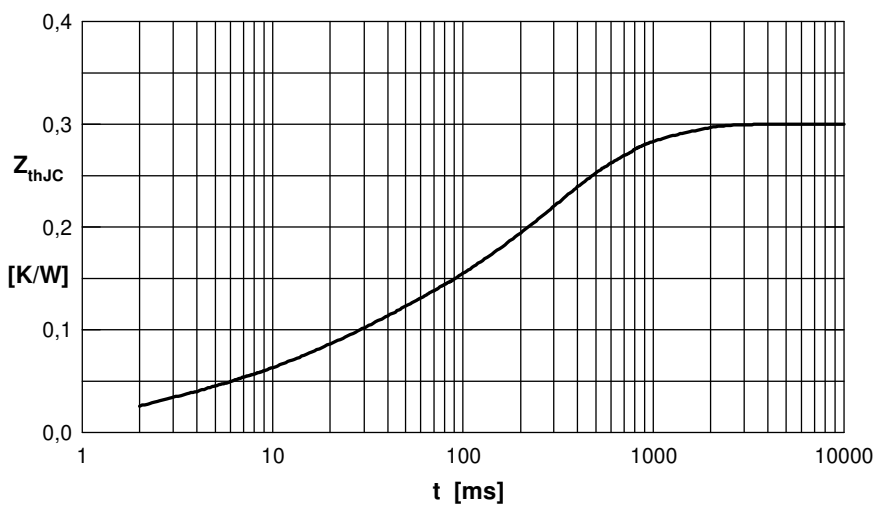


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.025	0.011
2	0.027	0.002
3	0.048	0.027
4	0.080	0.600
5	0.120	0.220